

# 74ABT623

Octal transceiver with dual enable; non-inverting; 3-state

Rev. 03 — 22 October 2009

Product data sheet

## 1. General description

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The 74ABT623 high performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT623 is an octal transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions. This octal bus transceiver is designed for asynchronous two-way communication between data buses.

The control function implementation allows maximum flexibility in timing. This device allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending upon the logic levels at the enable inputs (pins OEAB and  $\overline{\text{OEBA}}$ ). The enable inputs can be used to disable the device so that the buses are effectively isolated. The dual enable function configuration gives this transceiver the capability to store data by simultaneous enabling of pins OEAB and  $\overline{\text{OEBA}}$ . Each output reinforces its input in this transceiver configuration. Thus, when both control inputs are enabled and all other data sources to the two sets of the bus lines are at high-impedance OFF-state, both sets of the bus lines will remain at their last states. The 8-bit codes appearing on the two sets of buses will be identical.

## 2. Features

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- Octal bidirectional bus interface
- 3-state buffers
- Power-up 3-state
- Output capability: +64 mA and -32 mA
- data inputs are disabled during 3-state mode
- Latch-up protection exceeds 500 mA per JESD78B class II level A
- ESD protection:
  - ◆ HBM JESD22-A114F exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V

### 3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74ABT623D	-40 °C to +85 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74ABT623DB	-40 °C to +85 °C	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1
74ABT623PW	-40 °C to +85 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1

### 4. Functional diagram

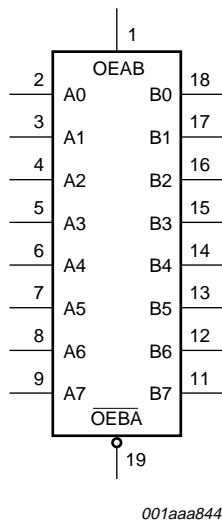


Fig 1. Logic symbol.

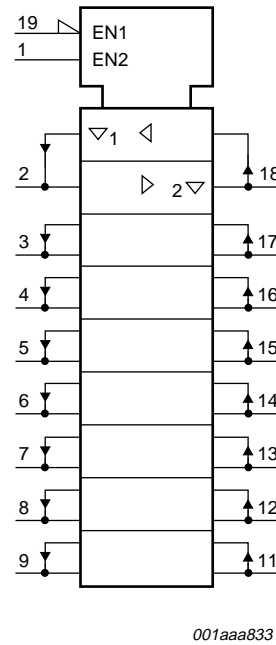


Fig 2. IEC logic symbol.

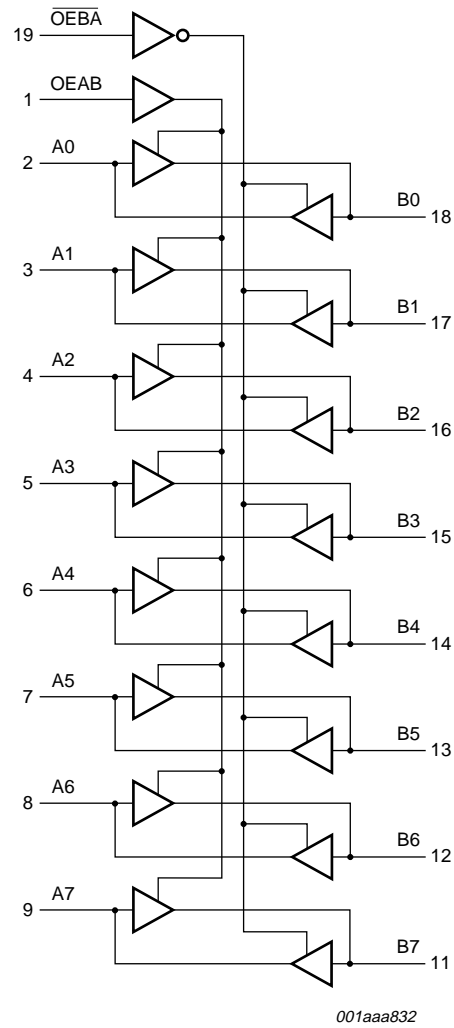


Fig 3. Logic diagram

## 5. Pinning information

### 5.1 Pinning

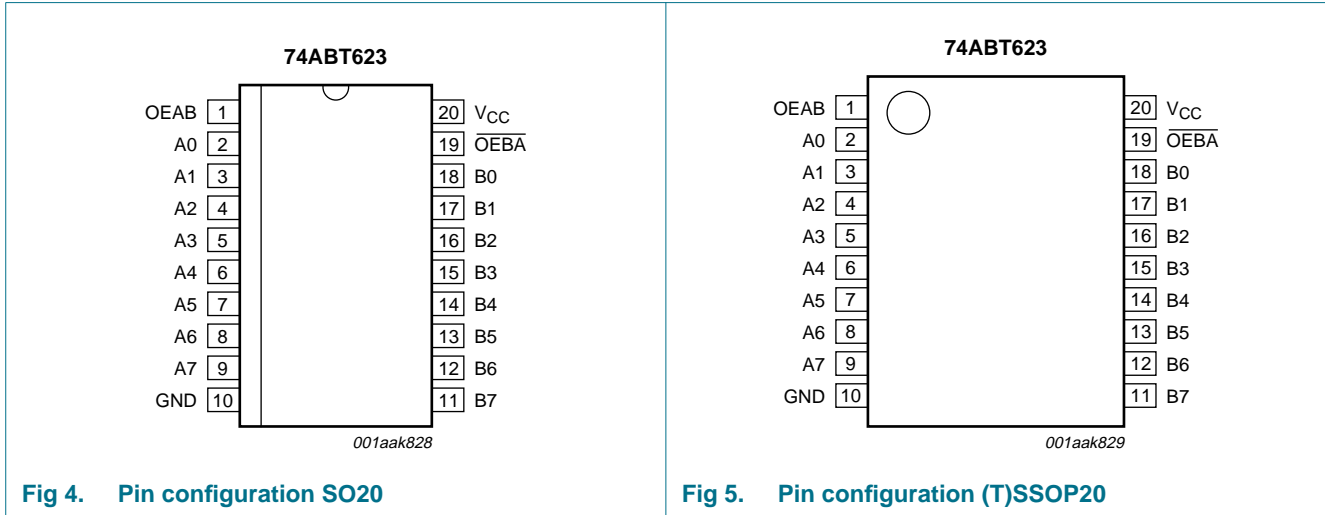


Fig 4. Pin configuration SO20

Fig 5. Pin configuration (T)SSOP20

### 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
OEAB	1	output enable input (active HIGH)
A0 to A7	2, 3, 4, 5, 6, 7, 8, 9	data input or output
B0 to B7	18, 17, 16, 15, 14, 13, 12, 11	data input or output
GND	10	ground (0 V)
OEBA	19	output enable input (active LOW)
V <sub>CC</sub>	20	supply voltage

## 6. Functional description

Table 3. Function table<sup>[1]</sup>

Input		Input or output	
OEAB	OEBA	A <sub>n</sub>	B <sub>n</sub>
L	L	A <sub>n</sub> = B <sub>n</sub>	input
H	H	input	B <sub>n</sub> = A <sub>n</sub>
L	H	Z	Z
H	L	A <sub>n</sub> = B <sub>n</sub>	input
H	L	input	B <sub>n</sub> = A <sub>n</sub>

[1] H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF-state.

## 7. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
$V_I$	input voltage		[1] -1.2	+7.0	V
$V_O$	output voltage	output in OFF-state or HIGH-state	[1] -0.5	+5.5	V
$I_{IK}$	input diode current	$V_I < 0$ V	-18	-	mA
$I_{OK}$	output diode current	$V_O < 0$ V	-50	-	mA
$I_O$	output current	output in LOW-state	-	128	mA
$T_j$	junction temperature		[2] -	150	°C
$T_{stg}$	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation	$T_{amb} = -40$ °C to +85 °C	[3] -	500	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- [2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150 °C.
- [3] For SO20 package:  $P_{tot}$  derates linearly with 8 mW/K above 70 °C.  
For SSOP20 and TSSOP20 package:  $P_{tot}$  derates linearly with 5.5 mW/K above 60 °C.

## 8. Recommended operating conditions

**Table 5. Recommended operating conditions**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CC}$	supply voltage		4.5	-	5.5	V
$V_I$	input voltage		0	-	$V_{CC}$	V
$V_{IH}$	HIGH-level input voltage		2.0	-	-	V
$V_{IL}$	LOW-level input voltage		-	-	0.8	V
$I_{OH}$	HIGH-level output current		-32	-	-	mA
$I_{OL}$	LOW-level output current		-	-	64	mA
$\Delta t/\Delta V$	input transition rise or fall rate		0	-	10	ns/V
$T_{amb}$	ambient temperature	in free air	-40	-	+85	°C

9. Static characteristics

Table 6. Static characteristics

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		Unit	
			Min	Typ	Max	Min	Max		
V <sub>IK</sub>	input clamping voltage	V <sub>CC</sub> = 4.5 V; I <sub>IK</sub> = -18 mA	-	-0.9	-1.2	-	-1.2	V	
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IL</sub> or V <sub>IH</sub>							
		V <sub>CC</sub> = 4.5 V; I <sub>OH</sub> = -3 mA	2.5	2.9	-	2.5	-	V	
		V <sub>CC</sub> = 5.0 V; I <sub>OH</sub> = -3 mA	3.0	3.4	-	3.0	-	V	
		V <sub>CC</sub> = 4.5 V; I <sub>OH</sub> = -32 mA	2.0	2.4	-	2.0	-	V	
V <sub>OL</sub>	LOW-level output voltage	V <sub>CC</sub> = 4.5 V; I <sub>OL</sub> = 64 mA; V <sub>I</sub> = V <sub>IL</sub> or V <sub>IH</sub>	-	0.42	0.55	-	0.55	V	
I <sub>I</sub>	input leakage current	V <sub>CC</sub> = 5.5 V; V <sub>I</sub> = GND or 5.5 V							
		OEAB, OEBA	-	±0.01	±1.0	-	±1.0	µA	
		An, Bn	-	±5.0	±100	-	±100	µA	
I <sub>OFF</sub>	power-off leakage current	V <sub>CC</sub> = 0.0 V; V <sub>I</sub> or V <sub>O</sub> ≤ 4.5 V	-	±5.0	±100	-	±100	µA	
I <sub>O(pu/pd)</sub>	power-up/power-down output current	V <sub>CC</sub> = 2.0 V; V <sub>O</sub> = 0.5 V; V <sub>I</sub> = GND or V <sub>CC</sub> ; OEAB = GND; OEBA = V <sub>CC</sub>	[1]	-	±5.0	±50	-	±50	µA
I <sub>OZ</sub>	OFF-state output current	V <sub>CC</sub> = 5.5 V; V <sub>I</sub> = V <sub>IL</sub> or V <sub>IH</sub>							
		V <sub>O</sub> = 2.7 V	-	5.0	50	-	50	µA	
		V <sub>O</sub> = 0.5 V	-	-5.0	-50	-	-50	µA	
I <sub>LO</sub>	output leakage current	HIGH-state; V <sub>O</sub> = 5.5 V; V <sub>CC</sub> = 5.5 V; V <sub>I</sub> = GND or V <sub>CC</sub>	-	5.0	50	-	50	µA	
I <sub>O</sub>	output current	V <sub>CC</sub> = 5.5 V; V <sub>O</sub> = 2.5 V	[2]	-180	-100	-50	-180	-50	mA
I <sub>CC</sub>	supply current	V <sub>CC</sub> = 5.5 V; V <sub>I</sub> = GND or V <sub>CC</sub>							
		outputs HIGH-state	-	50	250	-	250	µA	
		outputs LOW-state	-	24	30	-	30	mA	
		outputs disabled	-	50	250	-	250	µA	
ΔI <sub>CC</sub>	additional supply current	per input pin; V <sub>CC</sub> = 5.5 V; one input pin at 3.4 V, other inputs at V <sub>CC</sub> or GND	[3]						
		outputs enabled	-	0.5	1.5	-	1.5	mA	
		outputs disabled	-	50	250	-	250	mA	
		one enable input at 3.4 V and other inputs at V <sub>CC</sub> or GND; outputs disabled	-	0.5	1.5	-	1.5	mA	
C <sub>I</sub>	input capacitance	V <sub>I</sub> = 0 V or V <sub>CC</sub>	-	4	-	-	-	pF	
C <sub>I/O</sub>	input/output capacitance	outputs disabled; V <sub>O</sub> = 0 V or V <sub>CC</sub>	-	7	-	-	-	pF	

[1] This parameter is valid for any V<sub>CC</sub> between 0 V and 2.1 V, with a transition time of up to 10 ms. From V<sub>CC</sub> = 2.1 V to V<sub>CC</sub> = 5 V ± 10 %, a transition time of up to 100 ms is permitted.

[2] Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

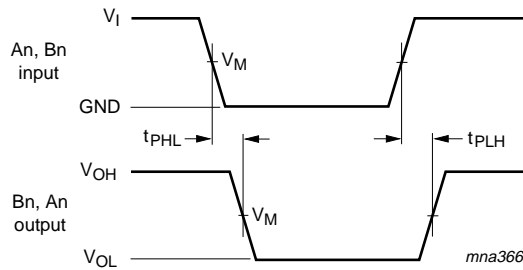
[3] This is the increase in supply current for each input at 3.4 V.

## 10. Dynamic characteristics

**Table 7. Dynamic characteristics**  
*GND = 0 V; for test circuit, see Figure 9.*

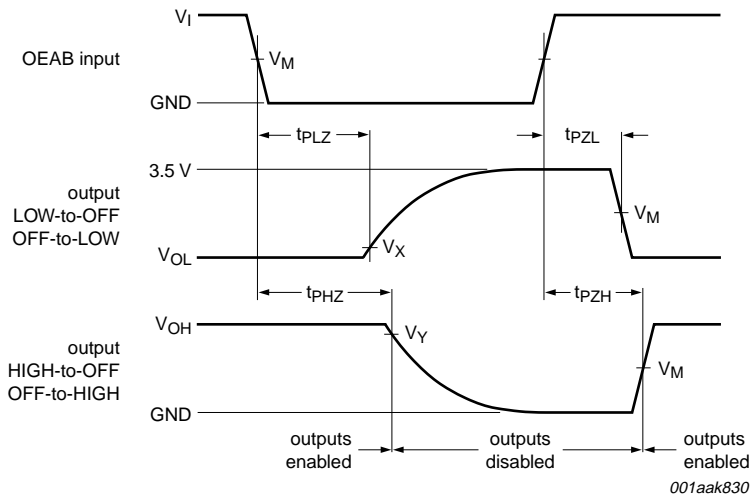
Symbol	Parameter	Conditions	25 °C; V <sub>CC</sub> = 5.0 V			-40 °C to +85 °C; V <sub>CC</sub> = 5.0 V ± 0.5 V		Unit
			Min	Typ	Max	Min	Max	
t <sub>PLH</sub>	LOW to HIGH propagation delay	An to Bn or Bn to An; see <a href="#">Figure 6</a>	1.0	2.6	4.1	1.0	4.6	ns
t <sub>PHL</sub>	HIGH to LOW propagation delay	An to Bn or Bn to An; see <a href="#">Figure 6</a>	1.0	2.7	4.2	1.0	4.6	ns
t <sub>PZH</sub>	OFF-state to HIGH propagation delay	OEAB, OEBA to An or Bn; see <a href="#">Figure 7</a> and <a href="#">Figure 8</a>	1.7	3.4	6.5	1.7	7.5	ns
t <sub>PZL</sub>	OFF-state to LOW propagation delay	OEAB, OEBA to An or Bn; see <a href="#">Figure 7</a> and <a href="#">Figure 8</a>	1.7	4.8	6.5	1.7	7.5	ns
t <sub>PHZ</sub>	HIGH to OFF-state propagation delay	OEAB, OEBA to An or Bn; see <a href="#">Figure 7</a> and <a href="#">Figure 8</a>	1.7	3.6	6.5	1.7	7.5	ns
t <sub>PLZ</sub>	LOW to OFF-state propagation delay	OEAB, OEBA to An or Bn; see <a href="#">Figure 7</a> and <a href="#">Figure 8</a>	1.7	3.1	6.5	1.7	7.5	ns

## 11. Waveforms



Measurement points are given in [Table 8](#).  
 V<sub>OL</sub> and V<sub>OH</sub> are typical voltage output levels that occur with the output load.

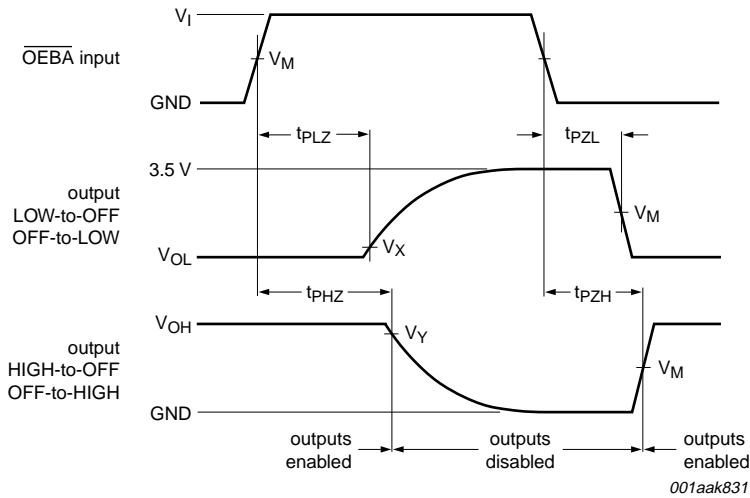
**Fig 6. Propagation delay input (An, Bn) to output (Bn, An)**



Measurement points are given in [Table 8](#).

$V_{OL}$  and  $V_{OH}$  are typical voltage output levels that occur with the output load.

**Fig 7. Enable and disable times for OEAB input.**



Measurement points are given in [Table 8](#).

$V_{OL}$  and  $V_{OH}$  are typical voltage output levels that occur with the output load.

**Fig 8. Enable and disable times for OEBA input.**

**Table 8. Measurement points**

Input		Output	
$V_I$	$V_M$	$V_X$	$V_Y$
3.0 V	1.5 V	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$



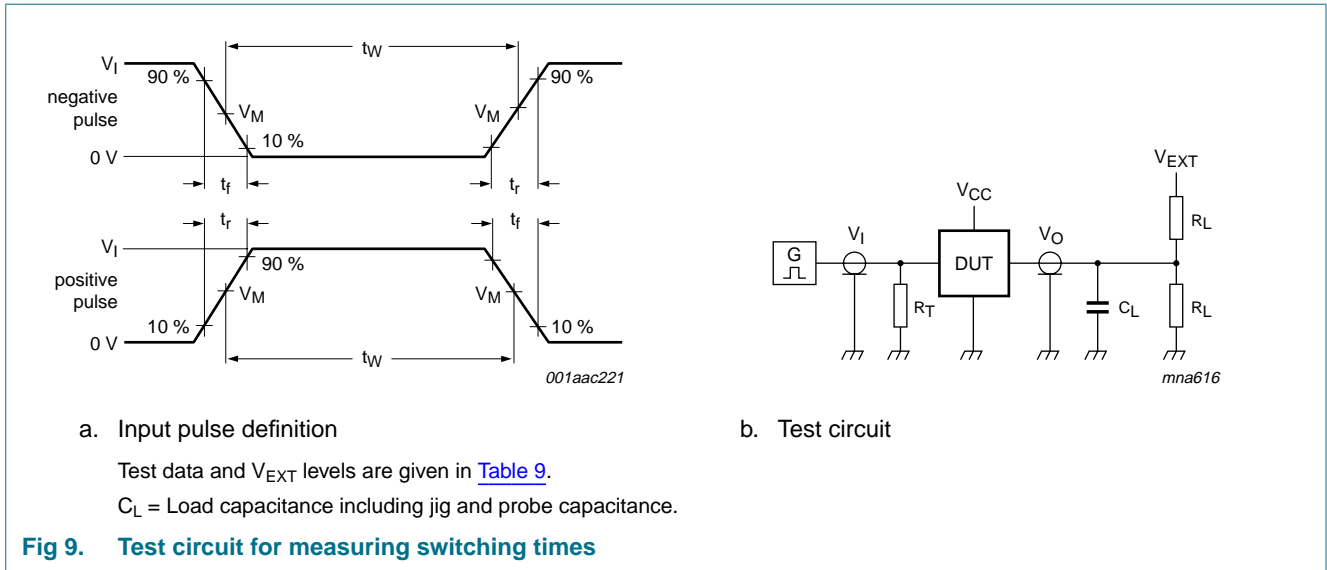


Table 9. Test data

Input	Load		$V_{EXT}$		
$t_r, t_f$	$C_L$	$R_L$	$t_{PHL}, t_{PLH}$	$t_{PZH}, t_{PHZ}$	$t_{PZL}, t_{PLZ}$
$\leq 2.5$ ns	50 pF	500 $\Omega$	open	open	7.0 V

12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1

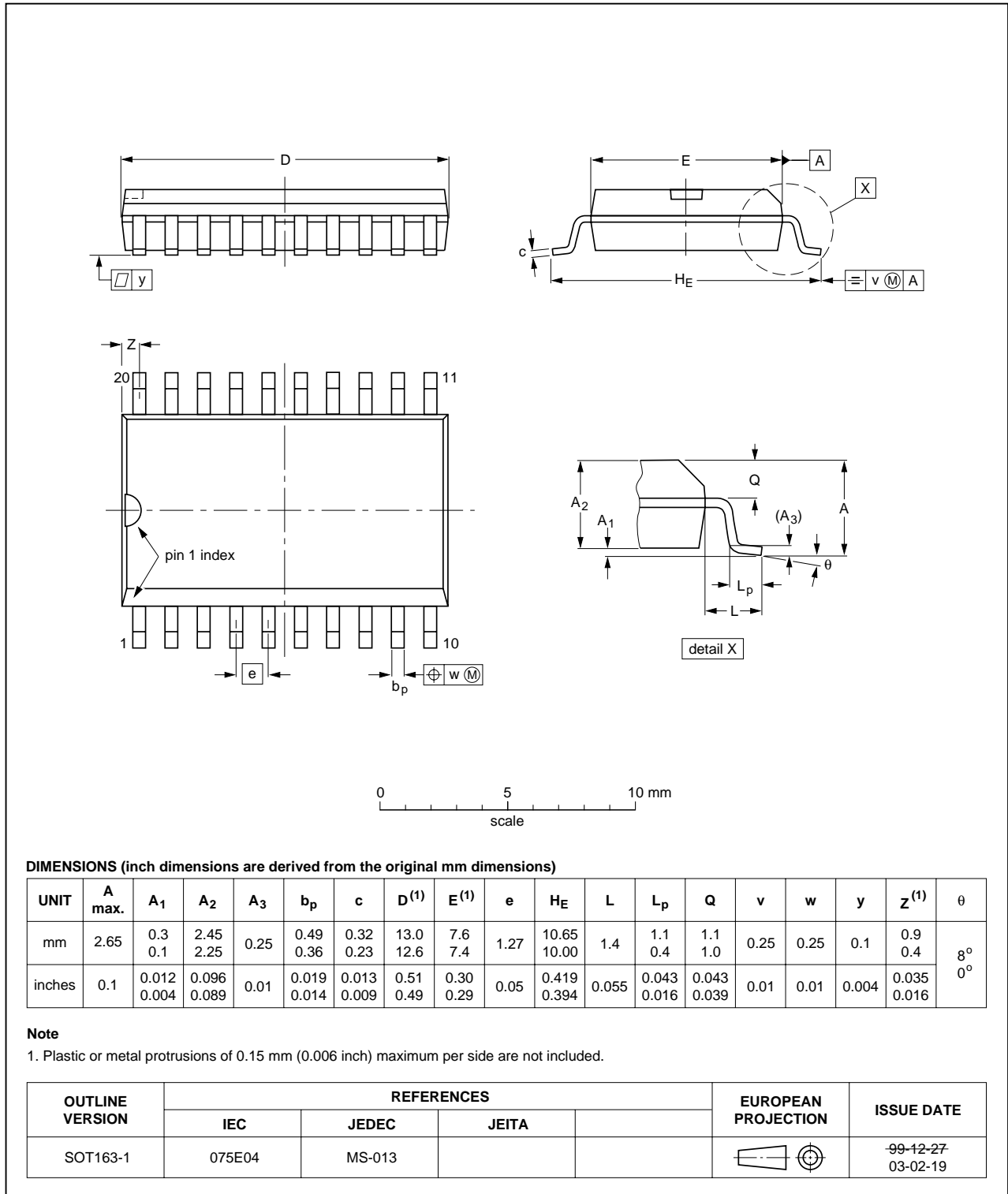


Fig 10. Package outline SOT163-1.

SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm

SOT339-1

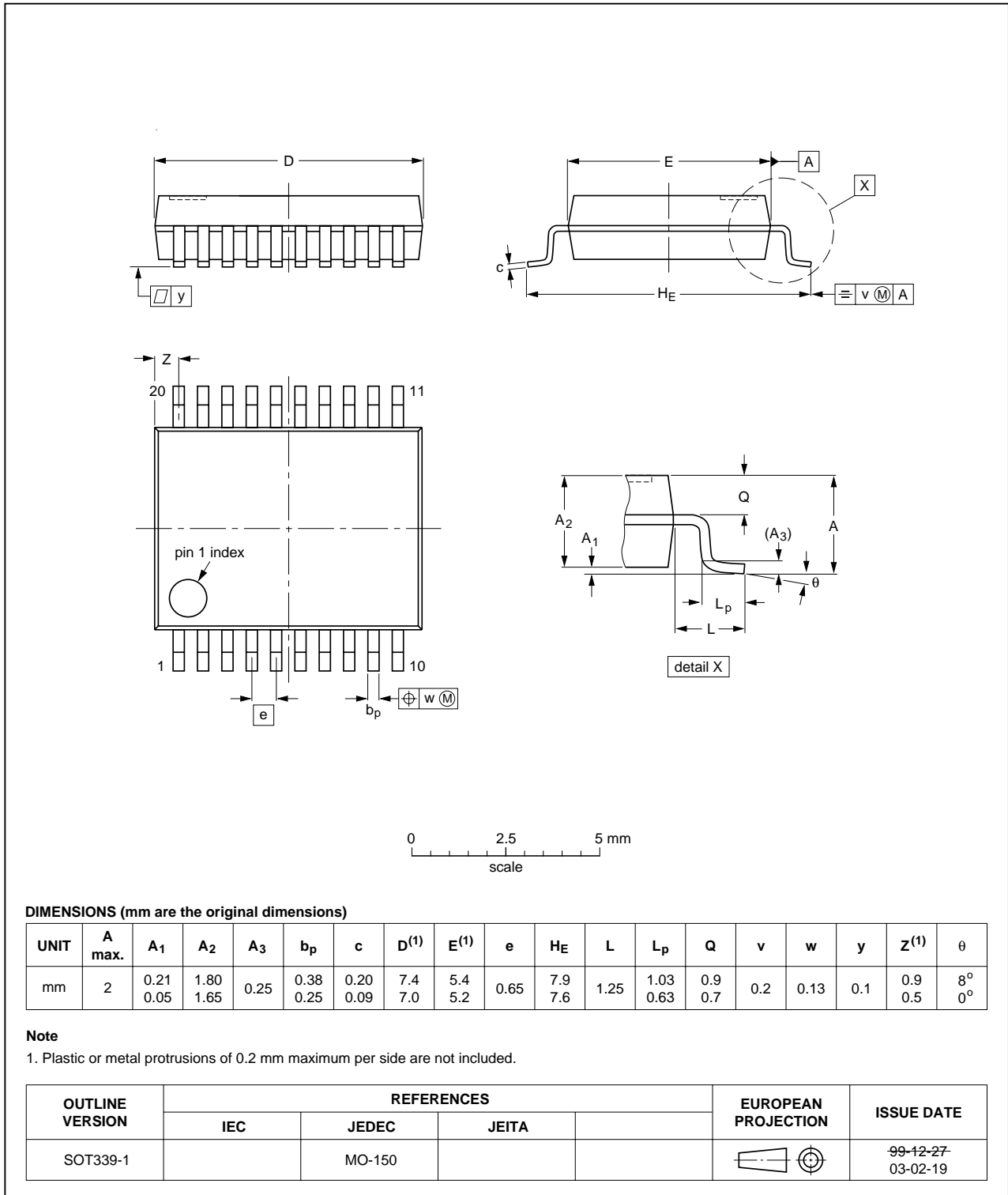


Fig 11. Package outline SOT339-1.

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1

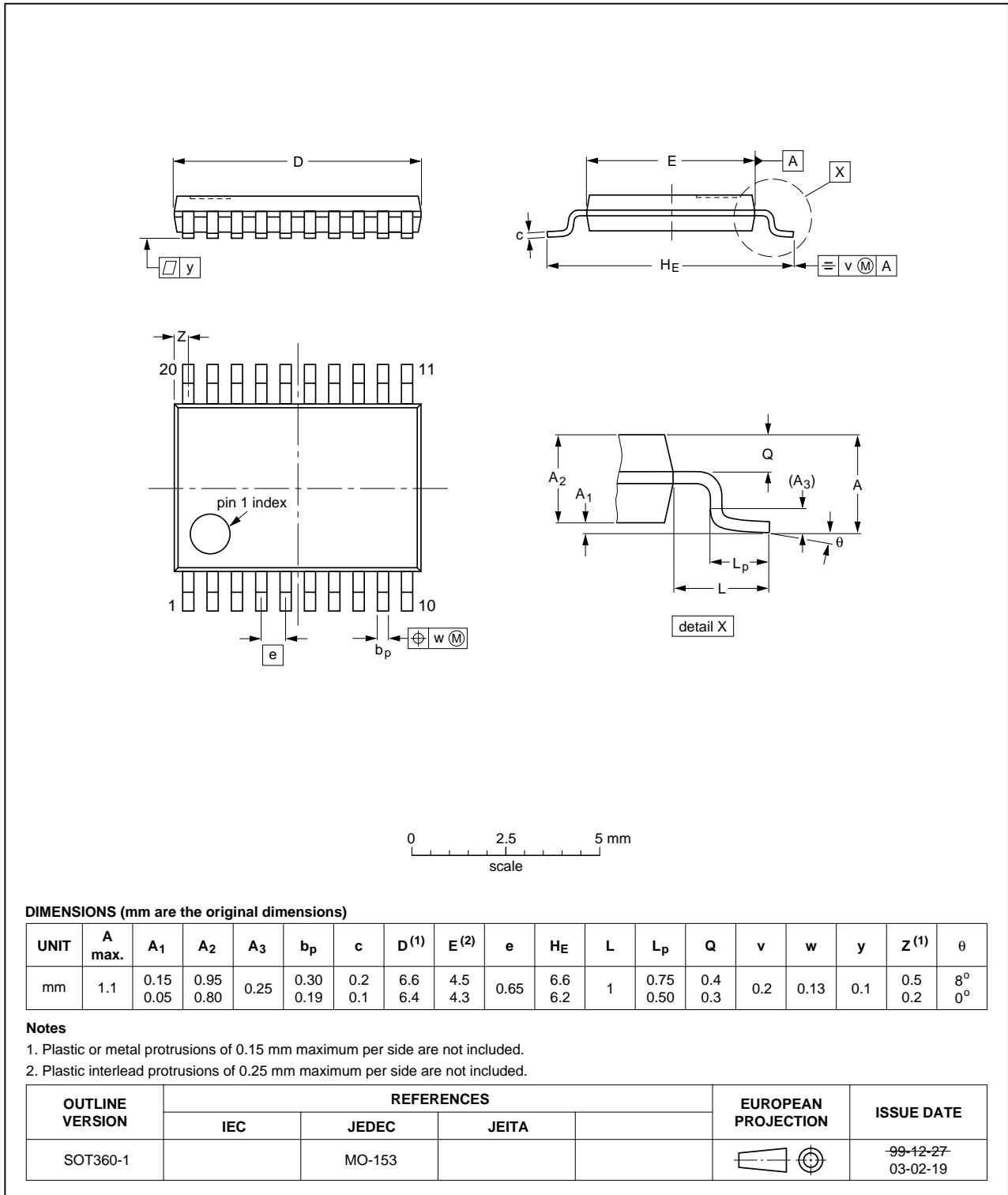


Fig 12. Package outline SOT360-1.

## 13. Abbreviations

Table 10. Abbreviations

Acronym	Description
BiCMOS	Bi-polar Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

## 14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74ABT623_3	20091022	Product data sheet	-	74ABT623_2
Modifications:		<ul style="list-style-type: none"><li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>• Legal texts have been adapted to the new company name where appropriate.</li><li>• DIP20 package removed from <a href="#">Section 3 “Ordering information”</a> and <a href="#">Section 12 “Package outline”</a>.</li></ul>		
74ABT623_2	19980116	Product specification	-	74ABT623_1
74ABT623_1	19960925	-	-	-

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### 15.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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